

L Number	Hits	Search Text	DB	Time stamp
-	14	(barrier adj layer) and (seed adj layer) and (release adj layer)	USPAT; US-PGPUB	2002/12/10 09:36
-	73	(method and copper adj interconnect\$4).ti.	USPAT; US-PGPUB	2002/12/06 13:03
-	84	(etch\$3 and copper and dielectric and (barrier adj layer) and (seed adj layer)).clm.	USPAT; US-PGPUB	2002/12/06 13:04
-	309	etch\$3 and ((barrier adj layer) and (seed adj layer)).clm.	USPAT; US-PGPUB	2002/12/06 13:10
-	482	etch\$3 and (copper adj interconnect\$4) and (barrier adj layer) and (seed adj layer)	USPAT; US-PGPUB	2002/12/10 09:50
-	4	etch\$3 and copper and ((conformal adj dielectric) and (seed adj layer)).clm.	USPAT; US-PGPUB	2002/12/10 07:49
-	288	etch\$3 and copper and ((barrier adj layer) and (seed adj layer)).clm.	USPAT; US-PGPUB	2002/12/09 10:55
-	42	copper adj interconnect\$4	JPO	2002/12/10 12:23
-	6	copper adj interconnect\$4	IBM_TDB	2002/12/10 07:56
-	103	(seed adj layer) and damascene adj interconnect	USPAT; US-PGPUB	2002/12/10 08:32
-	99	(damascene adj structure).ti.	USPAT; US-PGPUB	2002/12/10 08:33
-	57	damascene adj structure	JPO	2002/12/10 08:33
-	20	interconnect adj structure	JPO	2002/12/10 08:35
-	3	(barrier adj layer) and (seed adj layer) and photosensitive adj dielectric	USPAT; US-PGPUB	2002/12/10 09:13
-	5	photosensitive near5 (FSG or OSG or HSQ)	USPAT; US-PGPUB	2002/12/10 09:30
-	66	(phosphoric adj acid) same (nitric adj acid) same (acetic adj acid) same part same (etch\$3 or CMP)	USPAT; US-PGPUB	2002/12/10 09:40
-	76	(dielectric adj layer) and (aluminum adj layer) and (barrier adj layer) and (seed adj layer)	USPAT; US-PGPUB	2002/12/11 08:29
-	93	(copper adj interconnect\$4) and (void adj formation)	USPAT; US-PGPUB	2002/12/11 08:46
-	13	(conformal adj dielectric) and (barrier adj layer) and (seed adj layer)	USPAT; US-PGPUB	2002/12/11 08:39
-	14	(copper adj interconnect\$4).ti. and ((void adj formation) or (ion adj migration))	USPAT; US-PGPUB	2002/12/11 08:47
-	3	damascene same sidewall adj dielectric	USPAT; US-PGPUB	2002/12/11 10:15